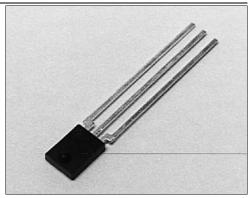
Optoschmitt Detector Open-Collector Output

FEATURES

- Side-looking plastic package
- 55° (nominal) acceptance angle
- TTL/LSTTL/CMOS compatible
- Open collector output
- Buffer (SDP8304) or inverting (SDP8314) logic available
- · High noise immunity output
- Mechanically and spectrally matched to SEP8506 and SEP8706 infrared emitting diodes



DESCRIPTION

The SDP8304/8314 series consists of a high speed IC molded in a side-looking black plastic package to minimize the effect of visible ambient light. The detector incorporates a Schmitt trigger which provides pulse shaping and hysteresis for noise immunity. Output rise and fall times are independent of rate of change of incident light. Detector sensitivity has been internally temperature compensated. The output stage is an open collector NPN transistor. This configuration allows the sensor to interface with circuit elements driven by supply voltages other than the V_{CC} supply. For additional output configuration options refer to SDP8004/8014 and SDP8604/8614.

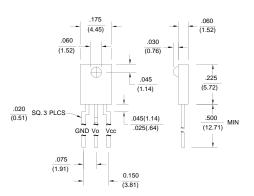
Device Polarity:

Buffer - Output is HI when incident light intensity is above the turn- on threshold level.

Inverter - Output is LO when incident light intensity is above the turn- on threshold level.

OUTLINE DIMENSIONS in inches (mm)

3 plc decimals ±0.005(0.12) 2 plc decimals ±0.020(0.51)



DIM_026.ds4



Optoschmitt Detector Open-Collector Output

ELECTRICAL CHARACTERISTICS (-40°C to +85°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Operating Supply Voltage	Vcc	4.5		12.0	V	T _A =25°C
Turn-on Threshold Irradiance (2) SDP8304-301, SDP8314-301	Еет(+)	0.06		0.37	mW/cm²	Vcc=5 V T _A =25°C
Hysteresis (3)	HYST	33		67	%	
Supply Current	lcc			15.0	mA	V _{CC} =12 V E _e =0 Or 3.0 mW/cm²
Low Level Output Voltage SDP8304 SDP8314	Vol			0.4 0.4	V	V _{CC} =5 V, I _{OL} =12.8 mA E _e =0 E _e =3.0 mW/cm ²
High Level Output Current SDP8304 SDP8314	Іон			100 100	μА	V_{CC} =4.5 V V_{OH} =30 V E_{e} =3.0 mW/cm ² E_{e} =0
Operate Point Temperature Coefficient			-0.76		%/°C	Emitter @ Constant Temperature
Output Rise Time, Output Fall Time	t _r , t _f		7.0		ns	V_{CC} =5 V, Ta=25°C Ee=0 or 3.0 mW/cm ² f=10.0 kHz, D.C.=50% R _L =390 Ω
Propagation Delay, Low-High, High-Low	трцн, трнц		2.5	5.0	μs	V _{CC} =5 V, T _A =25°C E _E =0.5 mW/cm ² f=10.0 kHz, D.C.=50% R _L =390 Ω
Clock Frequency				100	kHz	R _L =390 Ω, C _L =50 pF

- Notes

 1. It is recommended that a bypass capacitor, 0.1 µF typical, be added between V_{CC} and GND near the device in order to stabilize
- power supply limit of the control of operate threshold intensity.

ABSOLUTE MAXIMUM RATINGS SCHEMATIC SDP8304 BUFFER, OPEN-COLLECTOR (25°C Free-Air Temperature unless otherwise noted) Q Vcc Supply Voltage 12 V (1) **Duration of Output** Voltage Short to V_{CC} or Ground 1.0 sec regulator 35 V Applied Output Voltage Low Level Output Current 16 mA Irradiance 25 mW/cm² -40°C to 85°C Operating Temperature Range O Vo Storage Temperature Range -40°C to 85°C 240°C Soldering Temperature (5 sec)

Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

1. Derate linearly from 25°C to 5.5 V at 85°C.

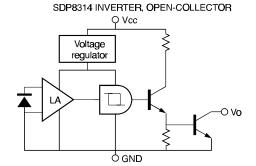
Honeywell

Ġ GND

Optoschmitt Detector Open-Collector Output

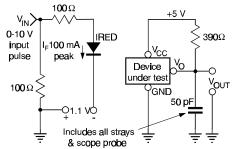
SCHEMATIC

SCH_019.cdr

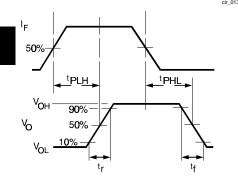


SWITCHING TIME TEST CIRCUIT

cir_007.cdr



SWITCHING WAVEFORM FOR BUFFERS



SWITCHING WAVEFORM FOR

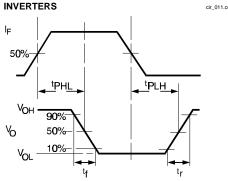


Fig. 1 Responsivity vs

Angular Displacement

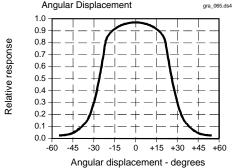
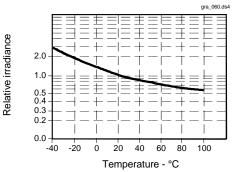


Fig. 2 Threshold Irradiance vs Temperature



Optoschmitt Detector Open-Collector Output

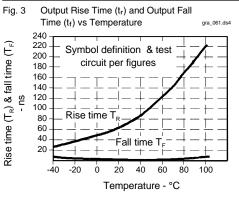
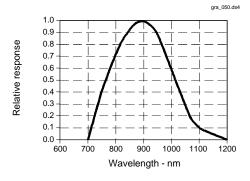


Fig. 5 Spectral Responsivity



All Performance Curves Show Typical Values